

PNZ108CL

Silicon NPN Phototransistor

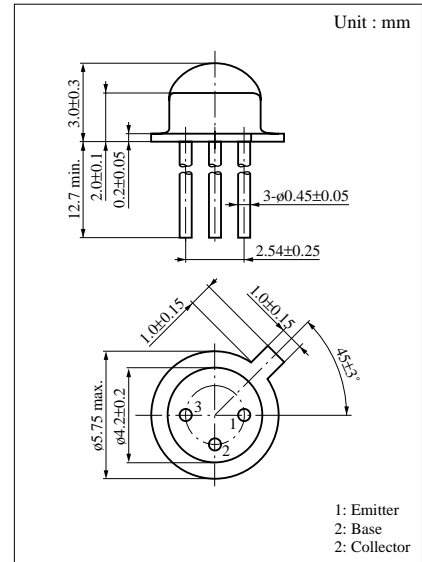
For optical control systems

■ Features

- High sensitivity : $I_{CE(L)} = 3.5 \text{ mA (min.)}$ (at $L = 500 \text{ lx}$)
- Wide directional sensitivity for easy use
- Fast response : $t_r = 5 \mu\text{s (typ.)}$
- Signal mixing capability using base pin
- Small size (low in height) package

■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to emitter voltage	V_{CEO}	20	V
Collector to base voltage	V_{CBO}	30	V
Emitter to collector voltage	V_{ECO}	3	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	20	mA
Collector power dissipation	P_C	100	mW
Operating ambient temperature	T_{opr}	-25 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}	-30 to +100	$^\circ\text{C}$

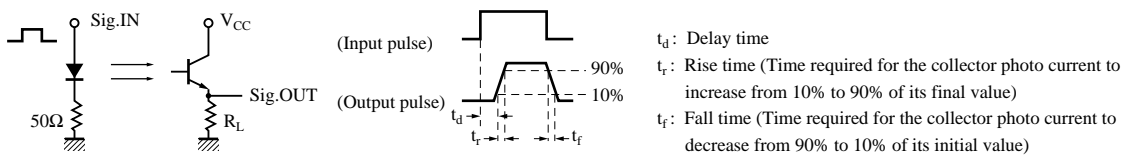


■ Electro-Optical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Dark current	I_{CEO}	$V_{CE} = 10\text{V}$		0.05	2	μA
Collector photo current	$I_{CE(L)}^{*3}$	$V_{CE} = 10\text{V}, L = 500 \text{ lx}^{*1}$	3.5	6		mA
Peak sensitivity wavelength	λ_p	$V_{CE} = 10\text{V}$		900		nm
Acceptance half angle	θ	Measured from the optical axis to the half power point		80		deg.
Rise time	t_r^{*2}	$V_{CC} = 10\text{V}, I_{CE(L)} = 5\text{mA}$		5		μs
Fall time	t_f^{*2}	$R_L = 100\Omega$		6		μs
Collector saturation voltage	$V_{CE(sat)}$	$I_{CE(L)} = 1\text{mA}, L = 1000 \text{ lx}^{*1}$		0.3	0.6	V

*1 Measurements were made using a tungsten lamp (color temperature $T = 2856\text{K}$) as a light source.

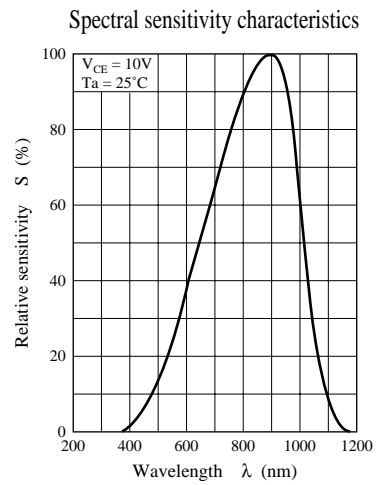
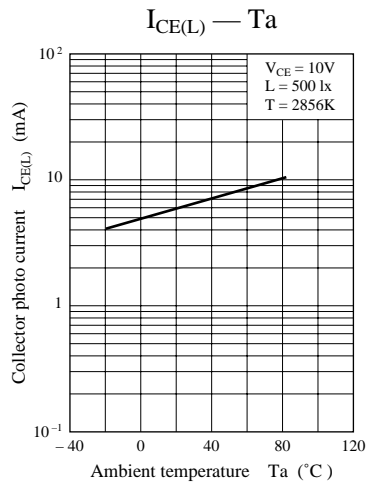
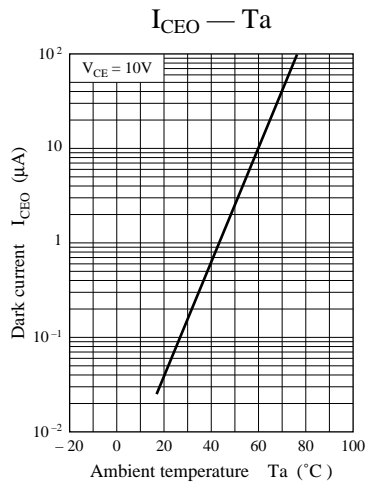
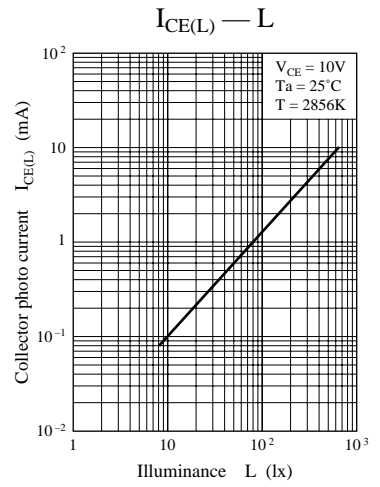
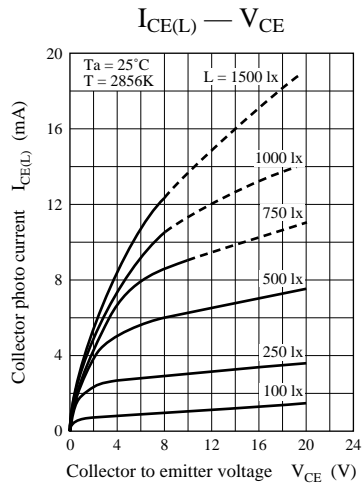
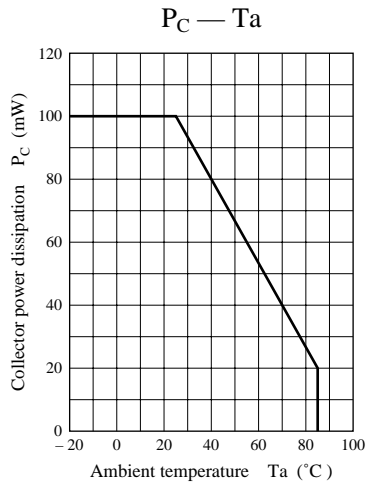
*2 Switching time measurement circuit



*3 $I_{CE(L)}$ Classifications

Class	Q	R	S
$I_{CE(L)}$ (mA)	3.5 to 6.0	5.0 to 9.1	> 7.5

Note) Difficult to guarantee compliance with moisture resistance standard (MIL-STD-202D).



Directivity characteristics

